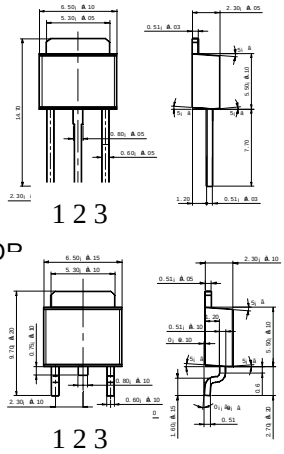
Transys Electronics LIMITED

TO-251 Plastic-Encapsulated Transistors

B772 TRANSISTOR (PNP)

TO-251
TO-252-2



1. BASE
2. COLLECTOR
3. EMITTER

FEATURES

Power dissipation

$P_{CM:}$ 1.25 W(Tamb=25℃)

Collector current

$I_{CM:}$ -3 A

Collector-base voltage

$V_{(BR)CBO}$: - 40 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= -100μA, I_E=0	-40			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	Ic= -10mA, I_B=0	-30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -100μA, I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}= -40V, I_E=0			-1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -30V, I_B=0			-10	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -6V, I_C=0			-1	μA
DC current gain	$h_{FE(1)}$	V_{CE}= -2V, IC= -1A	60		400	
	$h_{FE(2)}$	V_{CE}= -2V, I_C= -100mA	32			
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C= -2A, I_B= -0.2 A			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C= -2A, I_B= -0.2 A			-1.5	V
Transition frequency	f_T	V_{CE}= -5V, Ic=-0.1A f =10MHz	50			MHz

CLASSIFICATION OF hFE (1)

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400